



Subclass	ISSUE CLASSIFICATION
Class	

PATENT NUMBER

U.S. UTILITY Patent Application

O.I.P.E.	
SCANNED	TR3 Q.A.Ed

PATENT DATE

APPLICATION NO. 09/924318	CONT/PRIOR	CLASS 438	SUBCLASS 50	ART UNIT 1765	EXAMINER Tran, B
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APPLICANTS
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Fairborn, Asaadoekg.
Jack Mardalman

TITLE
Method of building a CMOS structure on thin Si with source/drain electrodes formed by an etched selectively amorphous silicon

PTO-2040
12/99

ISSUING CLASSIFICATION

ORIGINAL		CROSS REFERENCE(S)			
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)		
INTERNATIONAL CLASSIFICATION					

Continued on Issue Slip Inside File Jacket

TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	(Assistant Examiner) _____ (Date) _____			NOTICE OF ALLOWANCE MAILED	
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<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.	(Legal Instruments Examiner) _____ (Date) _____			Amount Due _____ Date Paid _____	

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